



SI4890DY-T1-E3 Information



For Reference Only

Part Number SI4890DY-T1-E3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 30V 11A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI4890DY-T1-E3 Specifications

Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C - Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 800mV @ 250µA (Min) Gate Charge (Qg) (Max) @ Vgs 20nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO		
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SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C-Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id800mV @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs20nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±25VFET Feature-Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 11A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET Type Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 11A, 10V Operating Temperature Supplier Device Package Package / Case N-Channel MOSFET (Metal Oxide) MOSFET (Metal Oxide) 30V	Package	8-SOIC (0.154", 3.90mm Width)
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Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	-
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±25V FET Feature - Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	800mV @ 250μA (Min)
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Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 11A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±25V
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Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	2.5W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	12 mOhm @ 11A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

SI4890DY-T1-E3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4890DY-T1-E3 Payment Methods



















SI4890DY-T1-E3 Shipping Methods













If you have any question about SI4890DY-T1-E3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com